

AMENDMENTS

In the Claims:

1. (Thrice Amended) A method of forming a fluorine doped insulating material comprising:

providing a substrate within a reaction chamber, the reaction chamber controlled within a range of temperatures from above 400 degrees Celsius ( $^{\circ}\text{C}$ ) but not greater than about  $700^{\circ}\text{C}$ ;

providing reactants comprising silicon, fluorine and ozone within the reaction chamber; and

depositing an insulating material, at a rate of from about 1000 angstroms per minute ( $\text{\AA}/\text{min}$ ) to about 10000  $\text{\AA}/\text{min}$ , comprising fluorine, silicon and oxygen onto the substrate from the reactants, wherein the depositing occurs with a plasma being present in the reaction chamber.

Please cancel Claims 3 and 11 without prejudice.

In Claim 18, replace "700" with --630--.

In Claim 20, replace "without" with --with--.

Please cancel Claim 21 without prejudice.

In Claim 22, replace "21" with --15--.

Sub 251  
C2  
23. (Thrice Amended) The method of Claim 1 wherein  
providing reactants comprising silicon, fluorine and ozone within the  
reaction chamber comprise providing reactants comprising triethoxy  
fluorosilane, a phosphorus-containing precursor and ozone, wherein the  
insulating material deposited is a phosphorus-doped silicon oxide material  
having Si-F bonds[, and the depositing occurring without a plasma being  
present in the reaction chamber].

Sub 251  
C3  
25. (Thrice Amended) The method of Claim 1 wherein  
providing reactants comprising silicon, fluorine and ozone within the  
reaction chamber comprises providing reactants that include triethoxy  
fluorosilane, a boron-containing precursor, a phosphorus-containing  
precursor and ozone, wherein the insulating material deposited is a boron  
and phosphorus-doped silicon oxide material having Si-F bonds[, and the  
depositing occurring without a plasma being present in the reaction  
chamber].

18 Please cancel Claims 35 and 37 without prejudice.

Sub 251  
C4  
38. The method of claim 18 comprising maintaining a pressure  
and a temperature within the reaction chamber at from about 400 Torr  
to about 1 atmosphere and in excess of 500°C but less than 630°C,  
respectively, during the depositing.

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In Claim 39, replace "18" with --38--.

Please cancel Claims 40-42 without prejudice.